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- (54) **Title:** METHOD OF INTEGRATED COPPER OXIDE REMOVAL AND LOW K REPAIR PROCESS

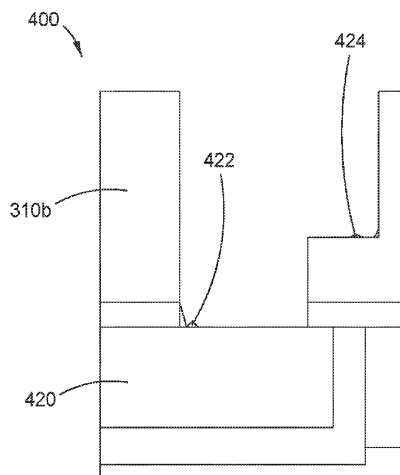


FIG. 4D

- (57) **Abstract:** A method for repairing copper and low-k dielectric films on a substrate is provided. In some embodiments, the method includes positioning the substrate within a process chamber, introducing a reducing agent into the process chamber to remove copper oxide from a copper layer on the substrate, removing the reducing agent from the process chamber, and introducing a recovery precursor into the process chamber to decrease a k value of a low-k film on the substrate.

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